

IXTH160N075T

Request a Quote

IXTH160N075T Information

	Part Number	IXTH160N075T	
	Manufacturer	IXYS	
www.helisener.com	Category	Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single	
1	Description	MOSFET N-CH 75V 160A TO-247	
-	Package	TO-247-3	
		For the pricing/inventory/lead time, please contact	
		us	
For Reference Only		Website: https://www.heisener.com	
		E-mail: salesdept@heisener.com	

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



IXTH160N075T Specifications

ManufacturerIXYSGategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTo-247-3SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°CI60A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs112nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4950pF @ 25VVgs (Max)-FET Feature-Power Dissipation (Max)Sidow (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTo-247 (IXTH)		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTo-247-3SeriesTrenchMY?SeriesTrenchMY?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°CI60A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs112nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4950pF @ 25VVgs (Max)560W (Tc)PET Feature-Power Dissipation (Max)6 mOhm @ 25A, 10VOperating Temperature55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTo-247-3	Manufacturer Part Number	IXTH160N075T
Transistors - FETs, MOSFETs - SinglePackageTO-247-3SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs112nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4950pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247.3	Manufacturer	IXYS
PackageTO-247-3SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vds112nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4950pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Category	Discrete Semiconductor Products
Series TrenchMV? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 75V Current - Continuous Drain (Id) @ 25°C 160A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 112nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4950pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package To-247 (IXTH) Package / Case TO-247-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vds4950pF @ 25VInput Capacitance (Ciss) (Max) @ Vds4950pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs55°C ~ 175°C (TJ)Operating Temperature55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Package	TO-247-3
Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 75V Current - Continuous Drain (Id) @ 25°C 160A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 112nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4950pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXTH) Package / Case TO-247-3	Series	TrenchMV?
Drain to Source Voltage (Vdss) 75V Current - Continuous Drain (Id) @ 25°C 160A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 112nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4950pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXTH)	FET Type	N-Channel
Current - Continuous Drain (ld) @ 25°С 160A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 112nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4950pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXTH) Package / Case TO-247-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 112nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4950pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXTH)	Drain to Source Voltage (Vdss)	75V
Vgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs112nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4950pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Current - Continuous Drain (Id) @ 25°C	160A (Tc)
Gate Charge (Qg) (Max) @ Vgs112nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4950pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds4950pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Vgs(th) (Max) @ Id	4V @ 250µA
Ygs (Max)±20VFET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	112nC @ 10V
FET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Input Capacitance (Ciss) (Max) @ Vds	4950pF @ 25V
Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Vgs (Max)	$\pm 20 \mathrm{V}$
Rds On (Max) @ Id, Vgs6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	FET Feature	-
Operating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Power Dissipation (Max)	360W (Tc)
Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Rds On (Max) @ Id, Vgs	6 mOhm @ 25A, 10V
Supplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247 (IXTH)
Report errors?	Package / Case	TO-247-3
		Report errors?

IXTH160N075T Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE EUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTH160N075T Payment Methods



IXTH160N075T Shipping Methods



If you have any question about IXTH160N075T, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com